

BCV62

PNP general-purpose double transistors

Rev. 4 — 26 July 2010

Product data sheet

1. Product profile

1.1 General description

PNP general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

| Type number | Package | | NPN complement |
|-------------|----------|-------|----------------|
| | Nexperia | JEITA | |
| BCV62 | SOT143B | - | BCV61 |
| BCV62A | | | BCV61A |
| BCV62B | | | BCV61B |
| BCV62C | | | BCV61C |

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- Applications with working point independent of temperature
- Current mirrors

1.4 Quick reference data

Table 2. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|---------------------------|--|-----|-----|------|------|
| Per transi | stor | | | | | |
| V_{CEO} | collector-emitter voltage | open base | - | - | -30 | V |
| I _C | collector current | | - | - | -100 | mA |
| Transisto | r TR1 | | | | | |
| h _{FE} | DC current gain | V_{CE} = -5 V; I_{C} = -100 μA | 100 | - | - | |
| | | $V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$ | 100 | - | 800 | |



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Table 2. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|-----------------|--|-----|-----|-----|------|
| Transistor | TR2 | | | | | |
| h _{FE} | DC current gain | $V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$ | | | | |
| | BCV62 | | 100 | - | 800 | |
| | BCV62A | | 100 | - | 250 | |
| | BCV62B | | 220 | - | 475 | |
| | BCV62C | | 420 | - | 800 | |

2. Pinning information

Table 3. Pinning

| Table 3. | Filling | | |
|----------|------------------------------------|--------------------|----------------|
| Pin | Description | Simplified outline | Graphic symbol |
| 1 | collector TR2; base TR1 and TR2 | 4 3 | 4 3 |
| 2 | collector TR1 | | 1 1 1 1 |
| 3 | emitter TR1 | | TR2 |
| 4 | emitter TR2 | 1 2 | 1 2 |
| | | | 006aaa843 |

3. Ordering information

Table 4. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BCV62 | - | plastic surface-mounted package; 4 leads | SOT143B |
| BCV62A | | | |
| BCV62B | | | |
| BCV62C | | | |

4. Marking

Table 5. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| BCV62 | 3M* |
| BCV62A | 3J* |
| BCV62B | 3K* |
| BCV62C | 3L* |

^{[1] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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Limiting values

Table 6. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|-----------------------------|-------|------|------|
| Per trans | sistor | | | | |
| V_{CBO} | collector-base voltage | open emitter | - | -30 | V |
| V_{CEO} | collector-emitter voltage | open base | - | -30 | V |
| V_{EBS} | emitter-base voltage | $V_{CE} = 0 V$ | - | -6 | V |
| I _C | collector current | | - | -100 | mA |
| I _{CM} | peak collector current | | - | -200 | mA |
| I_{BM} | peak base current | | - | -200 | mA |
| Per device | ce | | | | |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | [1] - | 250 | mW |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -65 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| | | | | | |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

Thermal characteristics

Thermal characteristics Table 7.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|-------------|-------|-----|-----|------|
| $R_{th(j\text{-}a)}$ | thermal resistance from junction to ambient | in free air | [1] - | - | 500 | K/W |

^[1] Device mounted on an FR4 PCB.

Characteristics

Characteristics

 $T_i = 25$ °C unless otherwise specified.

| , | | | | | | |
|--------------------|--------------------------------------|--|-----|------|------------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Transistor | TR1 | | | | | |
| ODO | collector-base | $V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$ | - | - | -15 | nA |
| | cut-off current | $V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$ | - | - | - 5 | μΑ |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$ | - | - | -100 | nA |
| h _{FE} | DC current gain | $V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}$ | 100 | - | - | |
| | | $V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$ | 100 | - | 800 | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$ | - | -75 | -300 | mV |
| | | $I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$ | - | -250 | -650 | mV |

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Table 8. Characteristics ...continued $T_i = 25$ °C unless otherwise specified.

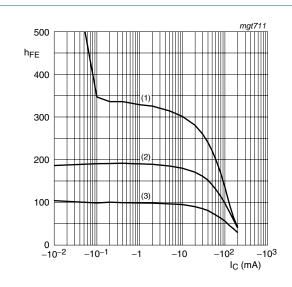
| $I_{B} = -5 \text{ mA}$ $V_{BE} \qquad \text{base-emitter voltage} \qquad \frac{I_{C} = -2 \text{ mA; V}_{CE} = -5 \text{ V}}{I_{C} = -10 \text{ mA; V}_{CE} = -5 \text{ V}} \qquad \frac{[2]}{I_{C}} = -600 \qquad -650$ $I_{C} = -10 \text{ mA; V}_{CE} = -5 \text{ V} \qquad \frac{[2]}{I_{C}} = -10 \text{ mA; V}_{CE} = -10 \text{ V} = -10 \text{ mA; V}_{CE} = -10 \text{ V} = -10 \text{ mA; V}_{CE} = -10 \text{ V} = -10 $ | - -750 -820 - | mV mV mV mV |
|---|------------------------|----------------------|
| $\begin{array}{c} I_{B} = -5 \text{ mA} \\ \\ V_{BE} \\ \\ Dase-emitter \ voltage \\ \hline \\ I_{C} = -2 \text{ mA}; \ V_{CE} = -5 \ V \\ \hline \\ I_{C} = -10 \text{ mA}; \ V_{CE} = -5 \ V \\ \hline \\ I_{C} = -10 \text{ mA}; \ V_{CE} = -5 \ V \\ \hline \\ I_{C} = -10 \text{ mA}; \ V_{CE} = -5 \ V \\ \hline \\ I_{C} = -10 \text{ mA}; \ V_{CE} = -5 \ V \\ \hline \\ I_{C} = -10 \text{ mA}; \ V_{CE} = -5 \ V; \ V_{CE} = -10 \ V_{CE} = -10 \ V; \ V_{CE} = -10 \ V_{CE} = -10 \ V; \ V_{CE} = -10 \ V_{CE} = -10 \ V; \ V_{CE} = -10 \ V_{CE} = -10 \ V_{CE} = -10 \ V; \ V_{CE} = -10 \ V_$ | -750 -820 - | mV mV |
| $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ | -820 - | mV |
| $\begin{array}{cccccccccccccccccccccccccccccccccccc$ | - | |
| $\begin{array}{c} I_C = -10 \text{ mA;} \\ f = 100 \text{ MHz} \end{array}$ $\begin{array}{c} C_c \\ \end{array} \begin{array}{c} \text{collector capacitance} \\ V_{CB} = -10 \text{ V;} \\ I_E = i_e = 0 \text{ A} \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} 4.5 \\ \end{array}$ $\begin{array}{c} \text{NF} \\ \end{array} \begin{array}{c} \text{noise figure} \\ V_{CE} = -5 \text{ V;} \\ I_C = -200 \mu\text{A;} \text{R}_S = 2 \text{ k}\Omega; \\ \text{f} = 1 \text{ kHz;} \text{B} = 200 \text{ Hz} \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{c} - \\ \end{array}$ | - | MHz |
| $I_E=i_e=0~A$ NF noise figure $V_{CE}=-5~V; \qquad -$ $I_C=-200~\mu\text{A}; R_S=2~k\Omega; \\ f=1~k\text{Hz}; B=200~\text{Hz}$ | _ | |
| $\begin{split} I_C &= -200 \; \mu\text{A}; R_S = 2 \; \text{k}\Omega; \\ f &= 1 \; \text{kHz}; \; \text{B} = 200 \; \text{Hz} \end{split}$ | _ | pF |
| Transistor TR2 | 10 | dB |
| | | |
| V_{EBS} emitter-base voltage $V_{CB} = 0 \text{ V; } I_E = -250 \text{ mA}$ - | -1.5 | ٧ |
| $V_{CB} = 0 \ V; I_E = -10 \ \mu A$ $-400 \ -$ | - | mV |
| h_{FE} DC current gain $V_{CE} = -5 \text{ V}; I_C = -2 \text{ mA}$ | | |
| BCV62 100 - | 800 | |
| BCV62A 100 - | 250 | |
| BCV62B 220 - | 475 | |
| BCV62C 420 - | 800 | |
| Transistors TR1 and TR2 | | |
| $I_{C1}/I_{E2} \qquad \text{current matching} \qquad \qquad I_{E2} = -0.5 \text{ mA}; \\ V_{CE1} = -5 \text{ V}; \qquad \qquad$ | | |
| $T_{amb} \le 25 ^{\circ}C$ 0.7 - | 1.3 | |
| $T_{amb} \le 150 ^{\circ}C$ 0.7 - | 1.3 | |
| I_{E2} emitter current 2 $V_{CE1} = -5 \text{ V}$ [3] | | mA |

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] Device, without emitter resistors, mounted on an FR4 PCB.

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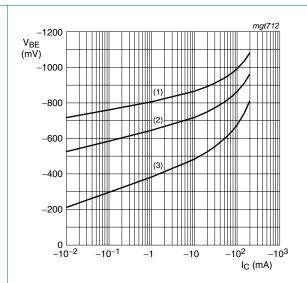
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. BCV62A: DC current gain as a function of collector current; typical values



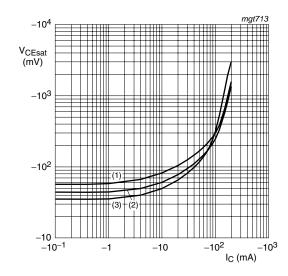
$$V_{\text{CE}} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 2. BCV62A: Base-emitter voltage as a function of collector current; typical values



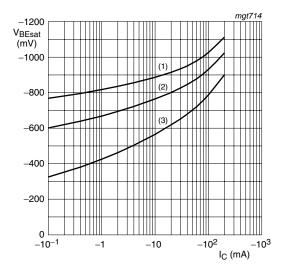
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. BCV62A: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

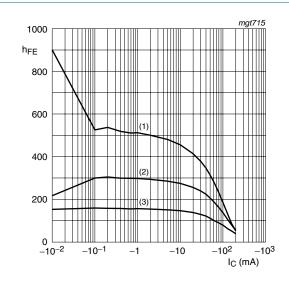
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. BCV62A: Base-emitter saturation voltage as a function of collector current; typical values

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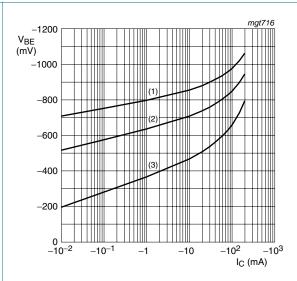
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 5. BCV62B: DC current gain as a function of collector current; typical values



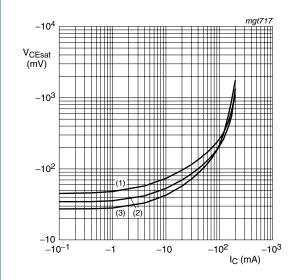
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 6. BCV62B: Base-emitter voltage as a function of collector current; typical values



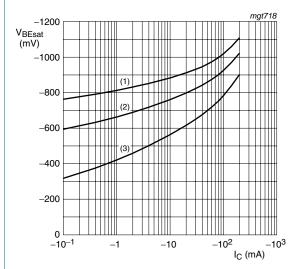
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. BCV62B: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

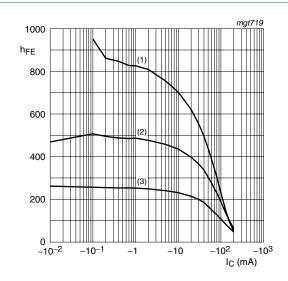
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 8. BCV62B: Base-emitter saturation voltage as a function of collector current; typical values

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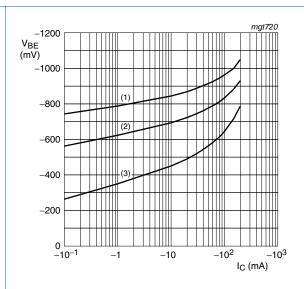
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 9. BCV62C: DC current gain as a function of collector current; typical values



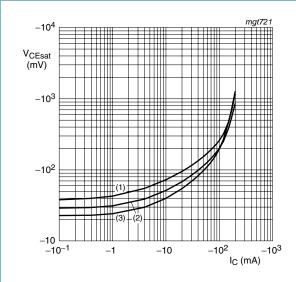
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 10. BCV62C: Base-emitter voltage as a function of collector current; typical values



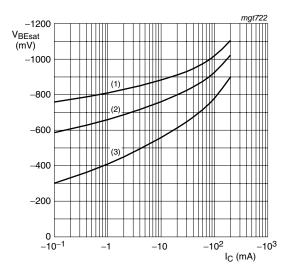
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 11. BCV62C: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

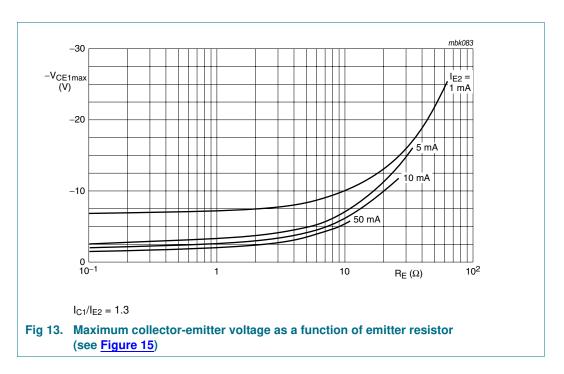
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

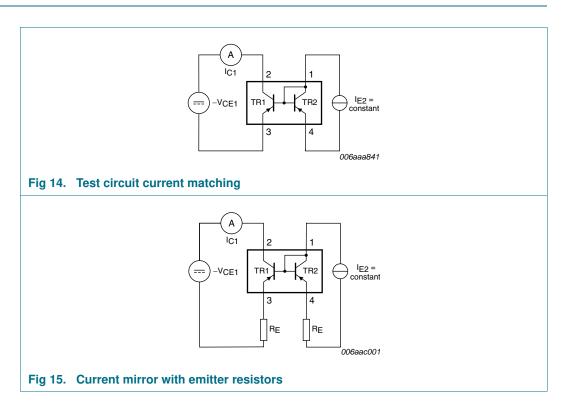
(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 12. BCV62C: Base-emitter saturation voltage as a function of collector current; typical values

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8. Test information

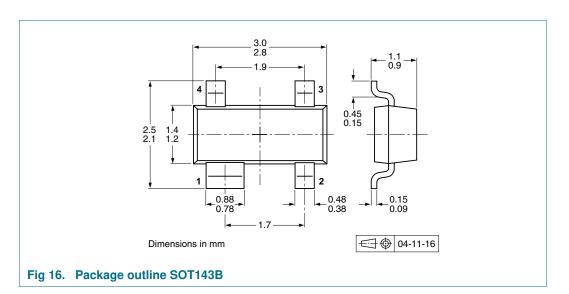


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8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

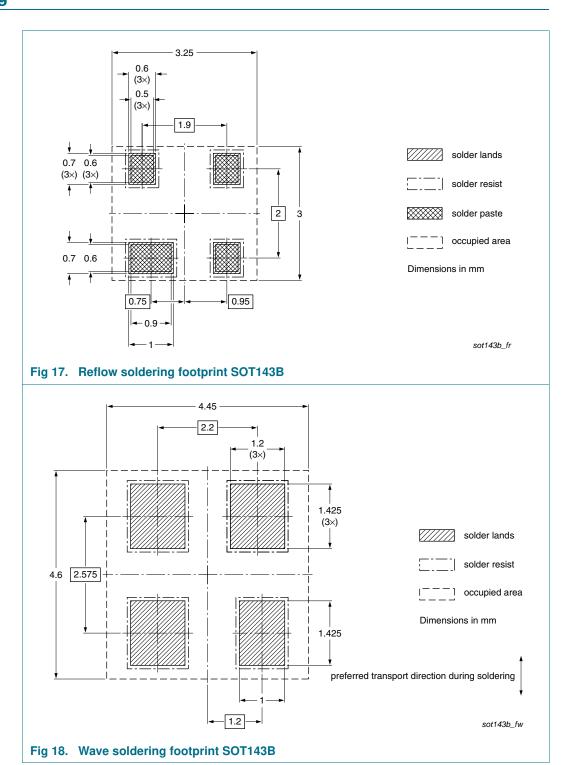
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | ckage Description I | | Packing quantity | | |
|-------------|---------|--------------------------------|------|------------------|--|--|
| | | | 3000 | 10000 | | |
| BCV62 | SOT143B | 4 mm pitch, 8 mm tape and reel | -215 | -235 | | |
| BCV62A | | | | | | |
| BCV62B | | | | | | |
| BCV62C | | | | | | |

^[1] For further information and the availability of packing methods, see $\underline{\text{Section 14}}$.

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11. Soldering



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12. Revision history

Table 10. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|----------------------------------|--|------------------------|-----------------------|
| BCV62 v.4 | 20100726 | Product data sheet | - | BCV62_3 |
| Modifications: | | of this data sheet has been of NXP Semiconductors. | redesigned to comply v | vith the new identity |
| | Legal texts | have been adapted to the ne | ew company name whe | ere appropriate. |
| | Section 1 "I | Product profile": amended | | |
| | Section 3 " | Ordering information": added | I | |
| | Section 4 "I | Marking": updated | | |
| | • Figure 1, 2, | 3, 4, 5, 6, 7, 8, 9, 10, 11 and | d <u>12</u> : added | |
| | Section 8 " | Test information": added | | |
| | • Figure 16: | superseded by minimized pa | ckage outline drawing | |
| | Section 10 | "Packing information": added | d | |
| | Section 11 | <u>"Soldering"</u> : added | | |
| | Section 13 | "Legal information": updated | | |
| BCV62_3 | 19990408 | Product specification | - | BCV62_CNV_2 |
| BCV62_CNV_2 | 19970618 | Product specification | - | - |
| | | | | |

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13. Legal information

13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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14. Contact information

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